Low Vcesat PNP Epitaxial Planar Transistor

BTA1952I3

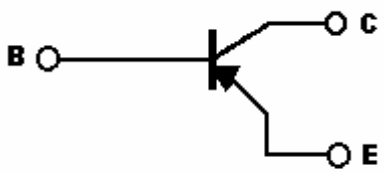
BV_{CEO}	-60V
I_C	-5A
R_{CESAT}	150mΩ

Features

- Low V_{CE}(sat), V_{CE}(sat)=-0.45 V (typical), at I_C / I_B = -3A / -0.15A
- Excellent DC current gain characteristics
- Wide SOA
- Complementary to BTC5103I3
- RoHS compliant package

Symbol

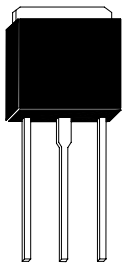
BTA1952I3



B：Base
C：Collector
E：Emitter

Outline

TO-251



B C E

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	$I_{C(DC)}$	-5	A
	$I_{C(Pulse)}$	-10 *1	
Power Dissipation	Pd(T_A=25℃)	1	W
	Pd(T_C=25℃)	25	
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

Note : *1. Single Pulse Pw=10ms

Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-100	-	-	V	I_C=-50μA, I_E=0
BV_{CEO}	-60	-	-	V	I_C=-10mA, I_B=0
BV_{EBO}	-5	-	-	V	I_E=-50μA, I_C=0
I_{CBO}	-	-	-1	μA	V_{CB}=-100V, I_E=0
I_{EBO}	-	-	-1	μA	V_{EB}=-5V, I_C=0
*$V_{CE(sat)}$	-	-0.45	-0.6	V	I_C=-3A, I_B=-0.15A
*$V_{BE(sat)}$	-	-	-1.2	V	I_C=-3A, I_B=-0.15A
*h_{FE} 1	70	-	240	-	V_{CE}=-1V, I_C=-1A
*h_{FE} 2	30	-	-	-	V_{CE}=-1V, I_C=-3A
f_T	-	60	-	MHz	V_{CE}=-4V, I_C=-1A, f=30MHz

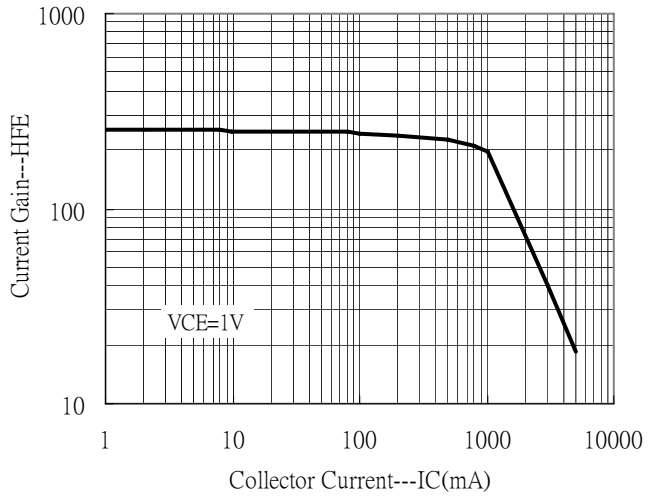
*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

Ordering Information

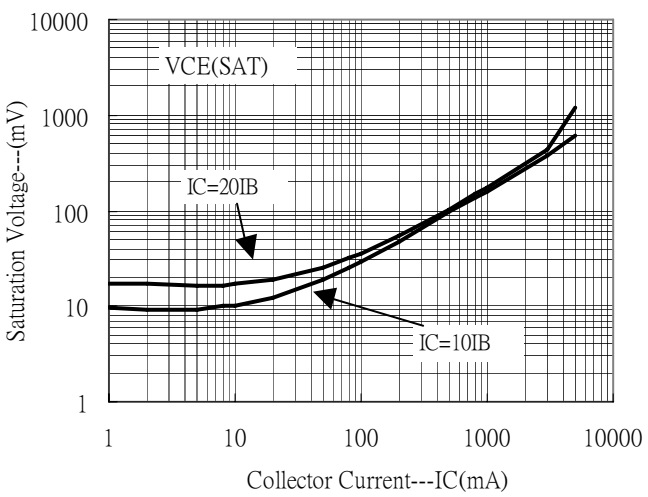
Device	Package	Shipping	Marking
BTA1952I3	TO-251 (RoHS compliant)	80 pcs / tube, 50 tubes / box	A1952

Characteristic Curves

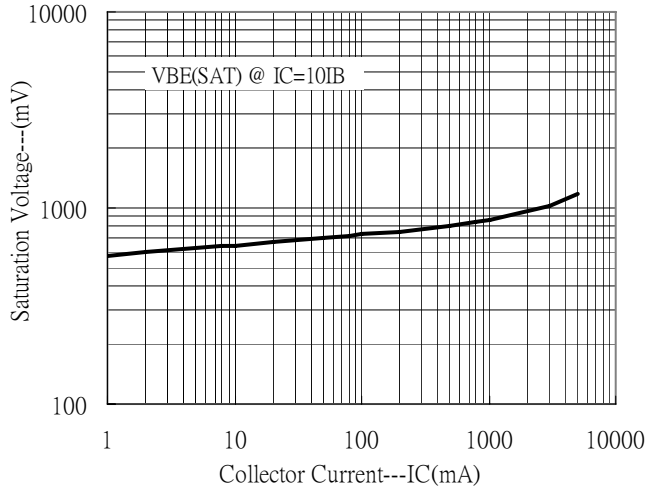
Current Gain vs Collector Current



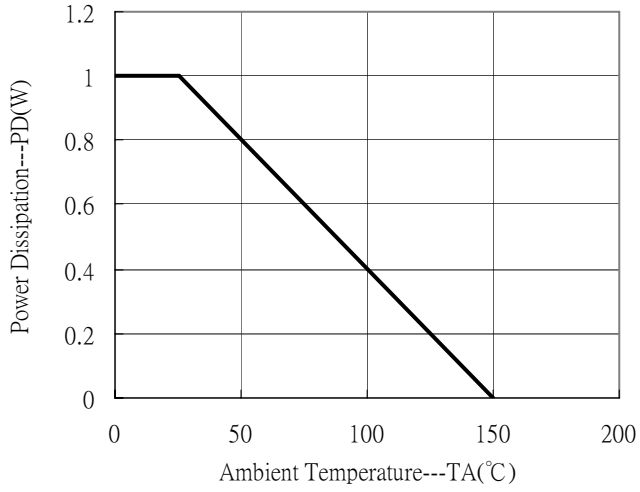
Saturation Voltage vs Collector Current



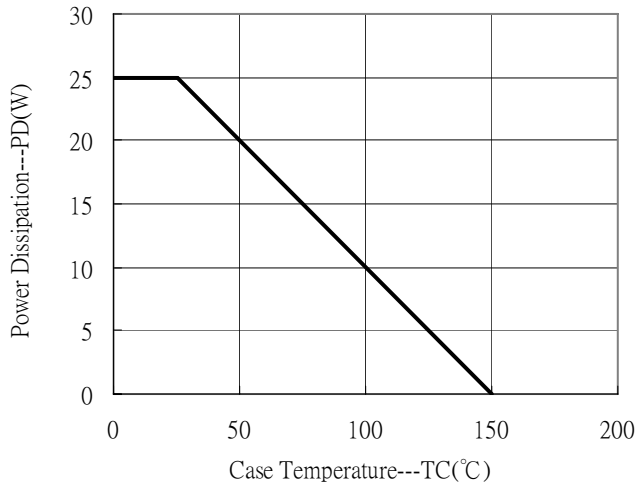
Saturation Voltage vs Collector Current



Power Derating Curve



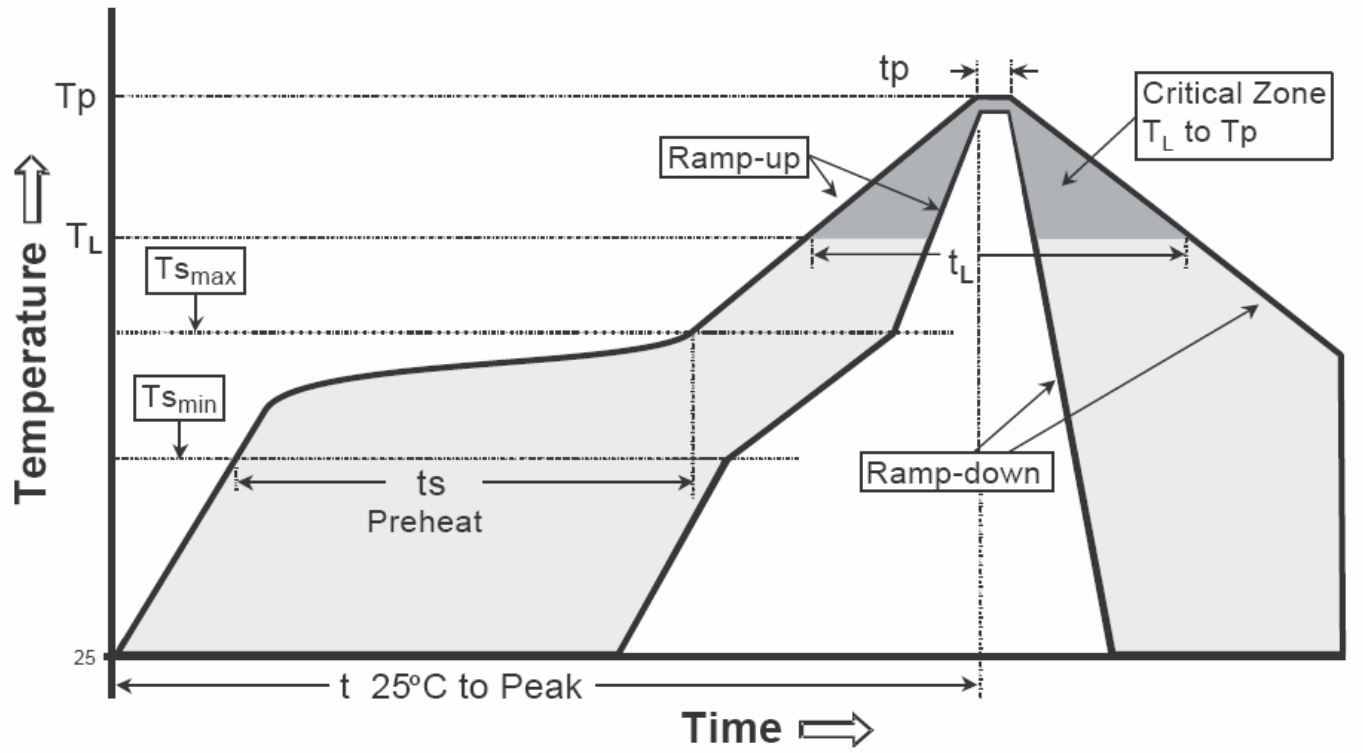
Power Derating Curve



Recommended wave soldering condition

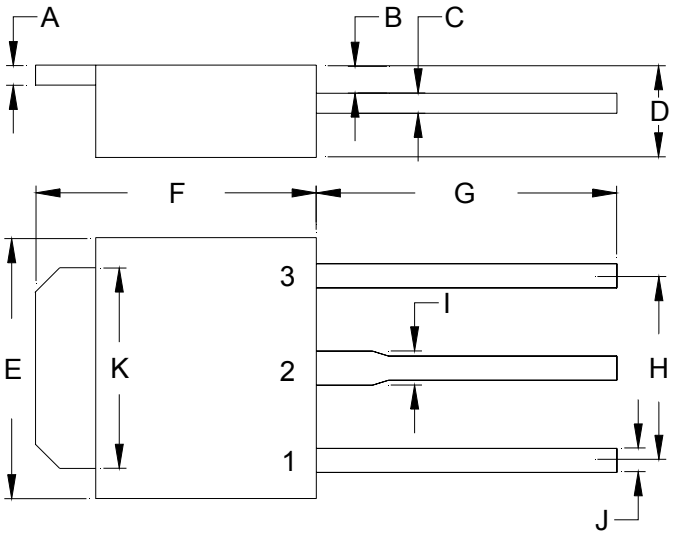
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

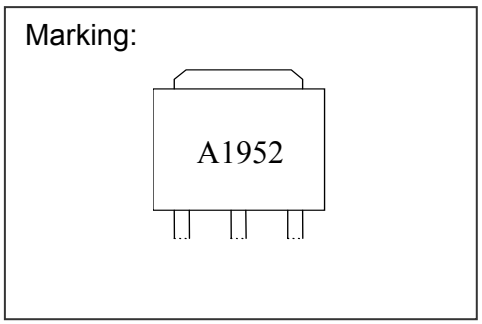
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat −Temperature Min(T_S min) −Temperature Max(T_S max) −Time($t_{s\ min}$ to $t_{s\ max}$)	 100°C 150°C 60-120 seconds	 150°C 200°C 60-180 seconds
Time maintained above: −Temperature (T_L) − Time (t_L)	 183°C 60-150 seconds	 217°C 60-150 seconds
Peak Temperature(T_P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

TO-251 Dimension





Style: Pin 1.Base 2.Collector 3.Emitter

3-Lead TO-251 Plastic Package
CYStek Package Code: I3

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0177	0.0217	0.45	0.55	G	0.2559	-	6.50	-
B	0.0354	0.0591	0.90	1.50	H	-	*0.1811	-	*4.60
C	0.0177	0.0236	0.45	0.60	I	-	0.0449	-	1.14
D	0.0866	0.0945	2.20	2.40	J	-	0.0346	-	0.88
E	0.2441	0.2677	6.20	6.80	K	0.2047	0.2165	5.20	5.50
F	0.2677	0.2835	6.80	7.20					

Notes: 1.Controlling dimension: millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: KFC; pure tin plated
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0